
FEATURES

- Ø 1.60 mm active area
- Low capacitance
- Long term stability
- High NIR sensitivity

DESCRIPTION

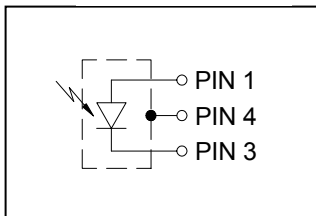
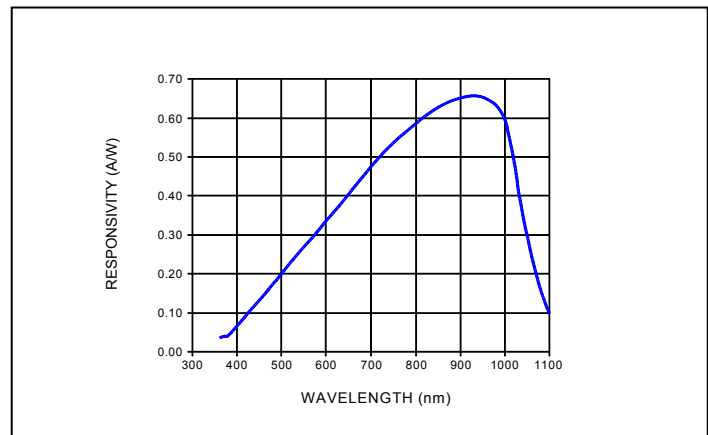
2.0 mm² Low Capacitance PIN Photodiode. Hermetically packaged in a TO-52-S1 with a clear borosilicate glass window cap.

APPLICATIONS

- Laser detection
- Instrumentation
- Optical remote control
- Pulsed light sensor


ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-55	+125	°C
T _{OP}	Operating Temp	-40	+100	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _(PEAK)	Peak DC Current	-	10	mA

SCHEMATIC

SPECTRAL RESPONSE

ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _D	Dark Current	V _R = 12 V	---	0.5	---	nA
C	Capacitance	V _R = 12 V	---	3.0	---	pF
	Responsivity	V _R = 0 V; λ = 950 nm	---	0.65	---	A/W
		V _R = 0 V; λ = 1064 nm	---	0.20	---	
NEP	Noise Equivalent Power	V _R = 12 V; λ = 850 nm; R _L = 50 Ω	---	1.0 × 10 ⁻¹⁴	---	W/Hz ^{1/2}
V _{BR}	Breakdown Voltage	I _R = 10 μA	30	---	---	V
t _r	Rise Time	V _R = 12 V; λ = 850 nm; R _L = 50 Ω	---	35	---	ns

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

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